MJE13005D

Preliminary

NPN SILICON TRANSISTOR

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

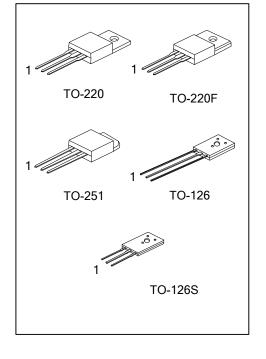
■ DESCRIPTION

The UTC **MJE13005D** is a high voltage fast-switching NPN power transistor. It is characterized by high breakdown voltage, high current capability, high switching speed and high reliability.

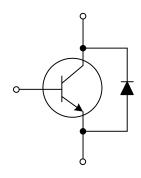
The UTC **MJE13005D** is intended to be used in energy-saving light, electronic ballast, high frequency switching power supply, high frequency power transform or common power amplifier, etc.

■ FEATURES

- * High Breakdown Voltage
- * High Current Capability
- * High Switching Speed
- * High Reliability
- * RoHS-Compliant Product

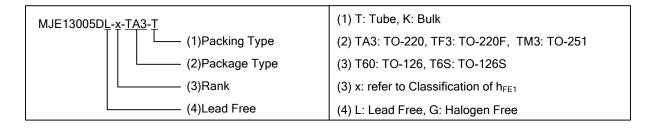


■ INTERNAL SCHEMATIC DIAGRAM



■ ORDERING INFORMATION

Ordering	Dookogo	Pin Assignment			Deaking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
MJE13005DL-x-TA3-T	MJE13005DG-x-TA3-T	TO-220	В	C	Е	Tube	
MJE13005DL-x-TF3-T	MJE13005DG-x-TF3-T	TO-220F	В	C	Е	Tube	
MJE13005DL-x-TM3-T	MJE13005DG-x-TM3-T	TO-251	В	С	Е	Tube	
MJE13005DL-x-T60-K	MJE13005DG-x-T60-K	TO-126	В	С	Е	Bulk	
MJE13005DL-x-T6S-K	MJE13005DG-x-T6S-K	TO-126S	В	С	E	Bulk	



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■ **ABSOLUTE MAXIMUM RATING** (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNIT
Collector- Emitter Voltage (V _{BE} =0)		V_{CES}	700	V
Collector-Emitter Voltage (I _B =0)		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	9	V
Collector Current	DC	Ic	4	Α
	Pulse	I _{CP}	8	Α
Base Current	DC	I _B	2	Α
	Pulse	I _{BP}	4	Α
Power Dissipation	TO-220/TO-220F		75	
	TO-251	P_{D}	50	W
	TO-126/TO-126S		45	
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT	
	TO-220/TO-220F		62.5		
Junction to Ambient	TO-251	θ_{JA}	110	°C/W	
	TO-126/TO-126S		89		
	TO-220/TO-220F		1.67		
Junction to Case	TO-251	θ_{JC}	2.5	°C/W	
	TO-126/TO-126S		2.78		

■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Collector-Emitter Breakdown Voltage		BV _{CEO}	I _C =10mA, I _B =0	400			٧	
Collector -Base Breakdown Voltage		BV_CBO	I _C =1mA, I _B =0	700			V	
Emitter-Base Breakdo	wn Voltage	BV_{EBO}	$I_E = 1 \text{mA}, I_C = 0$	9			V	
Collect Cut-off Current	t	I _{CBO}	V _{CB} =700V, I _E =0			100	μΑ	
Collect Cut-off Current		I _{CEO}	V _{CE} =400V,I _B =0			50	μΑ	
Emitter Cut-off Current		I _{EBO}	V _{EB} =9V, I _C =0			10	μΑ	
DC Current Gain		h _{FE1}	V _{CE} =5V, I _C =500mA 15			50		
		h _{FE2}	V_{CE} =5V, I_{C} =2A	5				
Collector-Emitter Saturation Voltage			I _C =1A, I _B =0.2A			0.5		
		V	I _C =2A, I _B =0.5A			0.6		
		V _{CE}	I _C =4A, I _B =1A			1		
			I _C =2A, I _B =0.5A, T _C =100°C			1		
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$	I _C =2A, I _B =0.5A			1.6	V	
Resistive Load	Fall Time	t_{F}	\/ -24\/ -24 - -0.44			0.7	μs	
	Storage Time	t _S	V _{CC} =24V, I _C =2A, I _{B1} =-I _{B2} =0.4A			4	μs	
Current Gain Bandwidth Product		f_T	V _{CE} =10V, I _C =0.5A	4			MH_Z	
Diode Forward Voltage		V_{F}	I _F =1A			1.5	V	

■ CLASSIFICATION OF h_{FE1}

RANK	Α	В	С	D	E
RANGE	15 ~ 20	20 ~ 25	25 ~ 30	30 ~ 40	40 ~ 50

^{2.} Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.

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